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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	508
Core Size	8-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SCI, SPI
Peripherals	LVD, PWM, WDT
Number of I/O	22
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512 x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	28-SOIC (0.295", 7.50mm Width)
Supplier Device Package	28-SOIC
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc9s08qe8cwl

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Freescale Semiconductor

Data Sheet: Technical Data

An Energy Efficient Solution by Freescale

Document Number: MC9S08QE8 Rev. 8, 4/2011

MC9S08QE8 Series

Covers: MC9S08QE8 and **MC9S08QE4**

Features

- 8-Bit HCS08 Central Processor Unit (CPU)
 - Up to 20 MHz CPU at 3.6 V to 1.8 V across temperature range of -40 °C to 85 °C
 - HC08 instruction set with added BGND instruction
 - Support for up to 32 interrupt/reset sources
- On-Chip Memory
 - Flash read/program/erase over full operating voltage and temperature
 - Random-access memory (RAM)
 - Security circuitry to prevent unauthorized access to RAM and flash contents
- · Power-Saving Modes
 - Two low power stop modes
 - Reduced power wait mode
 - Low power run and wait modes allow peripherals to run while voltage regulator is in standby
 - Peripheral clock gating register can disable clocks to unused modules, thereby reducing currents
 - Very low power external oscillator that can be used in stop2 or stop3 modes to provide accurate clock source to real time counter
 - 6 µs typical wake-up time from stop3 mode
- Clock Source Options
 - Oscillator (XOSC) Loop-control Pierce oscillator; crystal or ceramic resonator range of 31.25 kHz to 38.4 kHz or 1 MHz to 16 MHz
 - Internal Clock Source (ICS) Internal clock source module containing a frequency-locked-loop (FLL) controlled by internal or external reference; precision trimming of internal reference allows 0.2% resolution and 2% deviation over temperature and voltage; supporting bus frequencies from 1 MHz to 10 MHz
- System Protection
 - Watchdog computer operating properly (COP) reset with option to run from dedicated 1 kHz internal clock source or bus clock
 - Low-voltage warning with interrupt
 - Low-voltage detection with reset or interrupt
 - Illegal opcode detection with reset
 - Illegal address detection with reset
 - Flash block protection
- Development Support
 - Single-wire background debug interface
 - Breakpoint capability to allow single breakpoint setting during in-circuit debugging (plus two more breakpoints in on-chip debug module)

32-Pin QFN Case 2078-01

32-Pin LQFP Case 873A 28-Pin SOIC 751F-05



- On-chip in-circuit emulator (ICE) debug module containing two comparators and nine trigger modes; eight deep FIFO for storing change-of-flow addresses and event-only data; debug module supports both tag and force breakpoints
- Peripherals
 - ADC 10-channel, 12-bit resolution; 2.5 µs conversion time; automatic compare function; 1.7 mV/°C temperature sensor; internal bandgap reference channel; operation in stop3; fully functional from 3.6 V to 1.8 V
 - ACMPx Two analog comparators with selectable interrupt on rising, falling, or either edge of comparator output; compare option to fixed internal bandgap reference voltage; outputs can be optionally routed to TPM module; operation in stop3
 - SCI Full-duplex non-return to zero (NRZ); LIN master extended break generation; LIN slave extended break detection; wake-up on active edge
 - SPI Full-duplex or single-wire bidirectional; double-buffered transmit and receive; master or slave mode; MSB-first or LSB-first shifting
 - IIC Up to 100 kbps with maximum bus loading; multi-master operation; programmable slave address; interrupt driven byte-by-byte data transfer; supporting broadcast mode and 10-bit addressing
 - **TPMx** Two 3-channel (TPM1 and TPM2); selectable input capture, output compare, or buffered edge- or center-aligned PWM on each channel
 - RTC (Real-time counter) 8-bit modulus counter with binary or decimal based prescaler; external clock source for precise time base, time-of-day, calendar or task scheduling functions; free running on-chip low power oscillator (1 kHz) for cyclic wakeup without external components; runs in all MCU modes
- Input/Output
 - 26 GPIOs, one output-only pin and one input-only pin
 - Eight KBI interrupts with selectable polarity
 - Hysteresis and configurable pullup device on all input pins; configurable slew rate and drive strength on all output pins.
- Package Options
 - 32-pin LQFP, 32-pin QFN, 28-pin SOIC, 20-pin SOIC, 16-pin PDIP, 16-pin TSSOP

This document contains information on a product under development. Freescale reserves the right to change or discontinue this product without notice.

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Pin Assignments





Pins shown in bold type are lost in the next lower pin count package.





Pins shown in bold type are lost in the next lower pin count package.

Figure 4. MC9S08QE8 Series in 20-pin SOIC Package



	Pin N	umbei	r		< Lowest	t Priority	> Highest	
32	28	20	16	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4
26	26	20	16	PTA0	KBIP0	TPM1CH0	ADP0 ⁴	ACMP1+ ⁴
27	27	_		PTC7				ACMP2-
28	28	_		PTC6				ACMP2+
29	1	_	_	PTC5				ACMP2O
30	2	_		PTC4				
31	3	1	1	PTA5	IRQ	TCLK	RESET	
32	4	2	2	PTA4	ACMP1O	BKGD	MS	

Table 1. Pin Availability by Package Pin-Count (continued)

¹ IIC pins, SCL and SDA can be repositioned using IICPS in SOPT2, default reset locations are PTA3 and PTA2.

² TPM2CH2 pin can be repositioned using TPM2CH2PS in SOPT2, default reset location is PTA7.

³ TPM1CH2 pin can be repositioned using TPM1CH2PS in SOPT2, default reset location is PTA6.

⁴ If ADC and ACMP1 are enabled, both modules will have access to the pin.

3 Electrical Characteristics

3.1 Introduction

This section contains electrical and timing specifications for the MC9S08QE8 series of microcontrollers available at the time of publication.

3.2 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Р	Those parameters are guaranteed during production testing on each individual device.
С	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
Т	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

Table 2. Parameter Classifications

NOTE

The classification is shown in the column labeled "C" in the parameter tables where appropriate.

Rating	Symbol	Value	Unit
Operating temperature range (packaged)	T _A	T _L to T _H 40 to 85	°C
Maximum junction temperature	T _{JM}	95	°C
Thermal resistance Single-layer board			
32-pin QFN		110	
32-pin LQFP		66	
28-pin SOIC	0	57	°C/M
20-pin SOIC	AL	71	C/vv
16-pin PDIP		64	
16-pin TSSOP		108	
Thermal resistance Four-layer board			
32-pin QFN		42	
32-pin LQFP		47	
28-pin SOIC	٥	42	°C/M
20-pin SOIC	JA	52	0/00
16-pin PDIP		47	
16-pin TSSOP		78	

Table 4. T	hermal	Charact	eristics
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The average chip-junction temperature (T_J) in °C can be obtained from:

$$T_{J} = T_{A} + (P_{D} \times \theta_{JA})$$
 Eqn. 1

where:

 $\begin{array}{l} T_A = Ambient \ temperature, \ ^{\circ}C \\ \theta_{JA} = Package \ thermal \ resistance, \ junction-to-ambient, \ ^{\circ}C/W \\ P_D = P_{int} + P_{I/O} \\ P_{int} = I_{DD} \times V_{DD}, \ Watts \ -- \ chip \ internal \ power \\ P_{I/O} = Power \ dissipation \ on \ input \ and \ output \ pins \ -- \ user \ determined \end{array}$

For most applications, $P_{I/O} \ll P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$$P_{D} = K \div (T_{J} + 273 \ ^{\circ}C)$$
 Eqn. 2

Solving Equation 1 and Equation 2 for K gives:

K = P_D × (T_A + 273 °C) +
$$θ_{JA}$$
 × (P_D)² Eqn. 3

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Figure 10. Typical High-Side (Source) Characteristics — High Drive (PTxDSn = 1)

3.7 Supply Current Characteristics

This section includes information about power supply current in various operating modes.

Num	с	Parameter	Symbol	Bus Freq	V _{DD} (V)	Typical ¹	Max	Unit	Temp (°C)
1	Р	Run supply current	Blas	10 MHz		5.60	8.2	mA	-40 to 85 °C
	Т	FEI mode, all modules on	מטיי י	1 MHz	3	0.80	_		+010000
2	Т	Run supply current	Blas	10 MHz		3.60	—	mΔ	-40 to 85 °C
2	Т	FEI mode, all modules off	1 100	1 MHz	3	0.51	_		
3	т	Run supply current	Blaa	16 kHz FBILP	a	165	_		-40 to 85 °C
3	т	LPRS = 0, all modules off	DD	16 kHz FBELP	Iz P	105		μΑ	-40 10 85 0
4	Т	Run supply current	Blac	16 kHz FBILP	3	77	_	цА	-40 to 85 °C
	т	from flash	' "DD	16 kHz FBELP	5	21	_	μΛ	-40 10 85 0

Table 8. Supply Current Characteristics



3.10.3 SPI Timing

Table 14 and Figure 19 through Figure 22 describe the timing requirements for the SPI system.

No.	С	Function	Symbol	Min	Max	Unit
_	D	Operating frequency Master Slave	f _{op}	f _{Bus} /2048 0	f _{Bus} /2 f _{Bus} /4	Hz
1	D	SPSCK period Master Slave	t _{SPSCK}	2 4	2048 —	t _{cyc} t _{cyc}
2	D	Enable lead time Master Slave	t _{Lead}	1/2 1		t _{SPSCK} t _{сус}
3	D	Enable lag time Master Slave	t _{Lag}	1/2 1		t _{SPSCK} t _{сус}
4	D	Clock (SPSCK) high or low time Master Slave	twspsck	t _{cyc} – 30 t _{cyc} – 30	1024 t _{cyc}	ns ns
5	D	Data setup time (inputs) Master Slave	t _{SU}	15 15		ns ns
6	D	Data hold time (inputs) Master Slave	t _{HI}	0 25		ns ns
7	D	Slave access time	t _a	—	1	t _{cyc}
8	D	Slave MISO disable time	t _{dis}	—	1	t _{cyc}
9	D	Data valid (after SPSCK edge) Master Slave	t _v		25 25	ns ns
10	D	Data hold time (outputs) Master Slave	t _{HO}	0 0		ns ns
11	D	Rise time Input Output	t _{RI} t _{RO}		t _{cyc} – 25 25	ns ns
12	D	Fall time Input Output	t _{FI} t _{FO}		t _{cyc} – 25 25	ns ns

Table 14. SPI Timing





NOTES:

1. \overline{SS} output mode (DDS7 = 1, SSOE = 1).

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 19. SPI Master Timing (CPHA = 0)



NOTES:

1. SS output mode (DDS7 = 1, SSOE = 1).

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 20. SPI Master Timing (CPHA =1)

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Figure 23. ADC Input Impedance Equivalency Diagram

С	Characteristic	Conditions	Symbol	Min	Typ ¹	Мах	Unit	Comment
т	Supply current ADLPC = 1 ADLSMP = 1 ADCO = 1		I _{DDA}	_	120	_	μA	
т	Supply current ADLPC = 1 ADLSMP = 0 ADCO = 1		I _{DDA}	_	202	_	μA	
т	Supply current ADLPC = 0 ADLSMP = 1 ADCO = 1		I _{DDA}	_	288	_	μA	
Ρ	Supply current ADLPC = 0 ADLSMP = 0 ADCO = 1		I _{DDA}	_	0.532	1	mA	
Б	ADC	High speed (ADLPC = 0)	f	2	3.3	5		t _{ADACK} =
	clock source	Low power (ADLPC = 1)	IADACK	1.25	2	3.3	IVITIZ	1/f _{ADACK}

able 17. ADC Characteristics	(V _{REFH} =	V _{DDA} ,	V _{REFL} =	V _{SSA})	
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С	Characteristic	Conditions	Symbol	Min	Typ ¹	Мах	Unit	Comment	
	Conversion	Short sample (ADLSMP = 0)		_	20			See QE8	
Р	time (including sample time)	Long sample (ADLSMP = 1)	t _{ADC}	_	40		cycles	reference manual for	
_		Short sample (ADLSMP = 0)		_	3.5	_	ADCK	conversion time	
Р	Sample time	Long sample (ADLSMP = 1)	t _{ADS}	_	23.5	_	cycles	variances	
_	Temp sensor	–40 °C− 25 °C			1.646	—			
D	slope	25 °C– 85 °C	m	_	1.769	—	mv/°C		
D	Temp sensor voltage	25 °C	V _{TEMP25}	_	701.2	_	mV		
Ch	aracteristics for c	devices with dedicated analog su	upply (28- a	nd 32-p	oin packag	ges only)	•		
т		12-bit mode, 3.6> V _{DDA} > 2.7		_	-1 to 3	-2.5 to 5.5			
Т	Total unadjusted error	12-bit mode, 2.7> V _{DDA} > 1.8V	E _{TUE}	_	-1 to 3	-3.0 to 6.5	LSB ²	Includes	
Р		10-bit mode			±1	±2.5		quantization	
Ρ		8-bit mode			±0.5	±1.0			
Т		12-bit mode			±1.0	-1.5 to 2.0			
Р	Differential non-linearity	10-bit mode ³	DNL	_	±0.5	±1.0	LSB ²		
Р		8-bit mode ³		-	±0.3	±0.5			
т	Integral	12-bit mode			_	±1.5	–2.5 to 2.75		
Т	non-linearity	10-bit mode	INL		±0.5	±1.0	LSB ²		
Т		8-bit mode			±0.3	±0.5			
Т		12-bit mode			±1.5	±2.5			
Р	Zero-scale error	10-bit mode	E _{ZS}	-	±0.5	±1.5	LSB ²	V _{ADIN} = V _{SSA}	
Р		8-bit mode		_	±0.5	±0.5		00/1	
Т		12-bit mode		_	±1.0	-3.5 to 1.0			
Р	Full-scale error	10-bit mode	E _{FS}	_	±0.5	±1	LSB ²	V _{ADIN} = V _{DDA}	
Ρ		8-bit mode			±0.5	±0.5		BBR	
		12-bit mode		_	-1 to 0				
D	Quantization error	10-bit mode	EQ		_	±0.5	LSB ²		
		8-bit mode		_	_	±0.5			

Table 17. ADC Characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)



3.13 Flash Specifications

This section provides details about program/erase times and program-erase endurance for the flash memory.

Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see the Memory section.

С	Characteristic	Symbol	Min	Typical	Max	Unit	
D	Supply voltage for program/erase -40 °C to 85 °C	V _{prog/erase}	1.8	_	3.6	v	
D	Supply voltage for read operation	V _{Read}	1.8	—	3.6	V	
D	Internal FCLK frequency ¹	f _{FCLK}	150	—	200	kHz	
D	Internal FCLK period (1/FCLK)	t _{Fcyc}	5	—	6.67	μs	
Р	Byte program time (random location) ²	t _{prog}			t _{Fcyc}		
Р	Byte program time (burst mode) ²	t _{Burst}		4			
Р	Page erase time ²	t _{Page}			t _{Fcyc}		
Р	Mass erase time ²	t _{Mass}		20,000		t _{Fcyc}	
	Byte program current ³	RI _{DDBP}	_	4	—	mA	
	Page erase current ³	RI _{DDPE}	_	6	—	mA	
С	Program/erase endurance ⁴ T_L to $T_H = -40^{\circ}C$ to 85 °C $T = 25 ^{\circ}C$	·	10,000	100,000		cycles	
С	Data retention ⁵	t _{D_ret}	15	100	—	years	
1 The	frequency of this cleak is controlled by a coff	huara aatting	•			•	

The frequency of this clock is controlled by a software setting.

² These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

³ The program and erase currents are additional to the standard run I_{DD} . These values are measured at room temperatures with $V_{DD} = 3.0 \text{ V}$, bus frequency = 4.0 MHz.

⁴ Typical endurance for flash was evaluated for this product family on the 9S12Dx64. For additional information on how Freescale defines typical endurance, please refer to Engineering Bulletin EB619, *Typical Endurance for Nonvolatile Memory*.

⁵ Typical data retention values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale defines typical data retention, please refer to Engineering Bulletin EB618, *Typical Data Retention for Nonvolatile Memory.*

3.14 EMC Performance

Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.



Ordering Information

3.14.1 Conducted Transient Susceptibility

Microcontroller transient conducted susceptibility is measured in accordance with an internal Freescale test method. The measurement is performed with the microcontroller installed on a custom EMC evaluation board and running specialized EMC test software designed in compliance with the test method. The conducted susceptibility is determined by injecting the transient susceptibility signal on each pin of the microcontroller. The transient waveform and injection methodology is based on IEC 61000-4-4 (EFT/B). The transient voltage required to cause performance degradation on any pin in the tested configuration is greater than or equal to the reported levels unless otherwise indicated by footnotes below Table 19.

Parameter	Symbol	Conditions	f _{OSC} /f _{BUS}	Result	Amplitude ¹ (Min)	Unit		
				А	2.3			
Conducted susceptibility, electrical fast transient/burst (EFT/B)	V _{CS_EFT}	V _{DD} = 3.3 V T _A = 25 °C	8 MHz crystal	В	4.0	kV		
		03_211	CO_LI I	32-pin LQFP	8 MHz bus	С	>4.0	
				D	>4.0			

Table 19. Conducted Susceptibility, EFT/B

¹ Data based on qualification test results. Not tested in production.

The susceptibility performance classification is described in Table 20.

Table 20. Susc	eptibility Perfor	mance Classification
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Result		Performance Criteria				
A	No failure	The MCU performs as designed during and after exposure.				
В	Self-recovering failure	The MCU does not perform as designed during exposure. The MCU returns automatically to normal operation after exposure is removed.				
С	Soft failure	The MCU does not perform as designed during exposure. The MCU does not return to normal operation until exposure is removed and the RESET pin is asserted.				
D	Hard failure	The MCU does not perform as designed during exposure. The MCU does not return to normal operation until exposure is removed and the power to the MCU is cycled.				
E	Damage	The MCU does not perform as designed during and after exposure. The MCU cannot be returned to proper operation due to physical damage or other permanent performance degradation.				

4 Ordering Information

This section contains ordering information for the device numbering system.

Example of the device numbering system:







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TITLE:		DOCUMENT NE]: 98ASH70029A	REV: C
LOW PROFILE QUAD FLAT PA	ACK (LQFP)	CASE NUMBER	8: 873A-04	01 APR 2005
32 LEAD, 0.8 PITCH (7 X 7 X 1.4)		STANDARD: JE	DEC MS-026 BBA	





DETAIL G

SECTION F-F ROTATED 90°CW 32 PLACES



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TITLE: LOW PROFILE QUAD FLAT PACK (LQFP) 32 LEAD, 0.8 PITCH (7 X 7 X 1.4)		DOCUMENT NE]: 98ASH70029A	RE∨∶C
		CASE NUMBER: 873A-04 01 APR 2005		01 APR 2005
		STANDARD: JE	DEC MS-026 BBA	



NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.

2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5-1994.

 $\overline{3}$ datums a, b, and d to be determined at datum plane H.

 $\overline{/4.}$ dimensions to be determined at seating plane datum c.

5. DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED THE MAXIMUM DIMENSION BY MORE THAN 0.08 MM. DAMBAR CANNOT BE LOCATED ON THZ LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD OR PROTRUSION: 0.07 MM.

<u>6</u> DIMENSIONS DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 MM PER SIDE. DIMENSIONS ARE MAXIMUM PLASTIC BODY SIZE DIMENSIONS INCLUDING MOLD MISMATCH.

/7.\ EXACT SHAPE OF EACH CORNER IS OPTIONAL.

© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED.	MECHANICAL OUTLINE		PRINT VERSION NE	IT TO SCALE
TITLE:		DOCUMENT NE	: 98ASH70029A	RE∨: C
LOW PROFILE QUAD FLAT PACK (LQFP) 32 LEAD, 0.8 PITCH (7 X 7 X 1.4)		CASE NUMBER	: 873A-04	01 APR 2005
		STANDARD: JE	DEC MS-026 BBA	





© FREESCALE SEMICONDUCTOR, INC. All RIGHTS RESERVED.	MECHANICA	L OUTLINE	PRINT VERSION NO	DT TO SCALE
TITLE: SOIC, WIDE BODY, 28 LEAD CASEOUTLINE		DOCUMENT NO	: 98ASB42345B	REV: G
		CASE NUMBER: 751F-05 10 MAR 2003		10 MAR 2005
		STANDARD: MS	5-013AE	





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TITLE:	DOCUMENT NO): 98ASB42343B	REV: J	
20LD SOIC W/B, 1.27 PITCH		CASE NUMBER	R: 751D-07	23 MAR 2005
		STANDARD: JE	DEC MS-013AC	



NOTES:

- 1. DIMENSIONS ARE IN MILLIMETERS.
- 2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 3. DATUMS A AND B TO BE DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
- A. THIS DIMENSION DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSION OR GATE BURRS SHALL NOT EXCEED 0.15 MM PER SIDE. THIS DIMENSION IS DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
- 5. THIS DIMENSION DOES NOT INCLUDE INTER-LEAD FLASH OR PROTRUSIONS. INTER-LEAD FLASH AND PROTRUSIONS SHALL NOT EXCEED 0.25 MM PER SIDE. THIS DIMENSION IS DETERMINED AT THE PLANE WHERE THE BOTTOM OF THE LEADS EXIT THE PLASTIC BODY.
- 6. THIS DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.62 mm.

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TITLE:	DOCUMENT NO): 98ASB42343B	REV: J	
20LD SOIC W/B, 1.27 PITCH,		CASE NUMBER	2: 751D-07	23 MAR 2005
CASE OUTLINE		STANDARD: JE	DEC MS-013AC	







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TITLE:		DOCUMENT NE]: 98ASB42431B	REV: T
16 ID PDIP		CASE NUMBER	2: 648-08	19 MAY 2005
		STANDARD: NE	IN-JEDEC	





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TITLE: 16 LD TSSOP, PITCH 0.65MM		DOCUMENT NE	: 98ASH70247A	RE∨: B
		CASE NUMBER: 948F-01 19 MAY 200		
		STANDARD: JE	DEC	

